

IN THE CLAIMS:

Please amend the claims as follows:

Sub 1
B¹
4. (Amended) The method of claim 3, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B²
14. (Amended) The method of claim 13, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B³
16. (Amended) The method of claim 11, wherein said capped shallow trench isolation structure includes ledges which extend a [predetermined] distance over said upper surface of said semiconductor substrate adjacent said opposing trench edges.

B⁴
27. (Amended) The method of claim 26, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B⁵
35. (Amended) The method of claim 34, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B⁶
37. (Amended) The method of claim 33, wherein said capped shallow trench isolation structure includes ledges which extend a [predetermined] distance over said upper surface of said semiconductor substrate adjacent said opposing trench edges.